

CMOS - Sensor development for the ILC in Europe

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M. Szelezniak, I.Valin, **M. Winter (Project coordinator)**

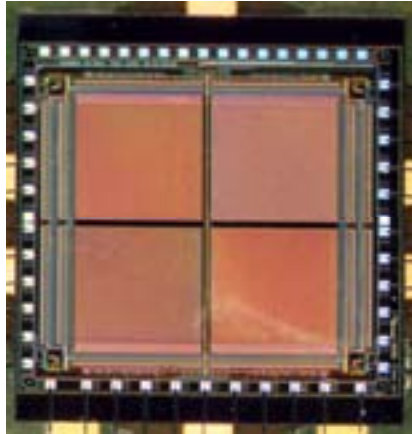
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CEA: Y. Derglerli, N. Fourches, Y. Li, P.Lutz, F. Orsini

Acknowledgements to the SUCIMA collaboration

The MIMOSA - Technology

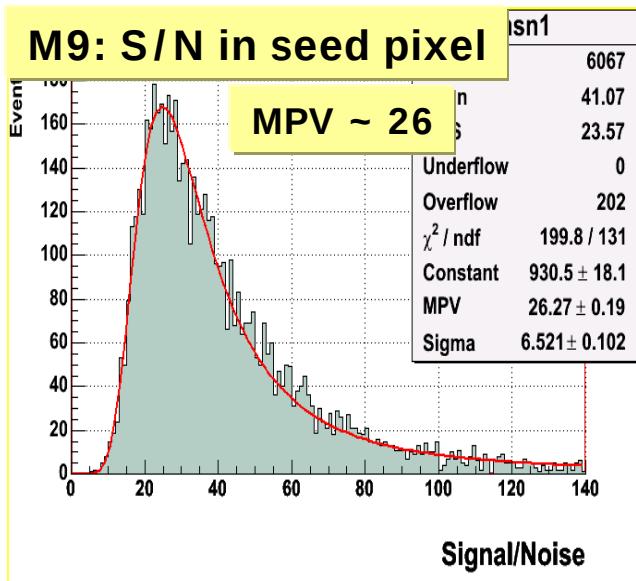
Minimum Ionizing Particle MOS Active Pixel Sensor



MIMOSA IV

M9: S/N in seed pixel

MPV ~ 26



Typical features of the MIMOSA – detectors:

20 μm pixel pitch, 12 bit serial readout:

- Single point resolution $1.5\mu\text{m} - 2.5\mu\text{m}$
- $\sigma_{2\text{hits}} \gtrsim 30 \mu\text{m}$
- S/N for MIPs ($\sim 100 \text{ GeV}/c$): 20-30 (MPV)
- Detection efficiency: $\epsilon_{\text{det}} \sim 99\text{-}99.9 \%$
- Standard sensor: 1MPixel, $120\mu\text{m}$ thickness
- 3 Wafers were thinned to $50\mu\text{m}$...*
- Produced in:
 - AMS- $0.6\mu\text{m}$, AMI- $0.35\mu\text{m}$, AMS- $0.35\mu\text{m}$,
 - AMS- $0.35\mu\text{m}$ opto, IBM- $0.25\mu\text{m}$, TSMC- $0.25\mu\text{m}$
- Further Applications: STAR, CBM

* see talk from H. Wieman, LBL

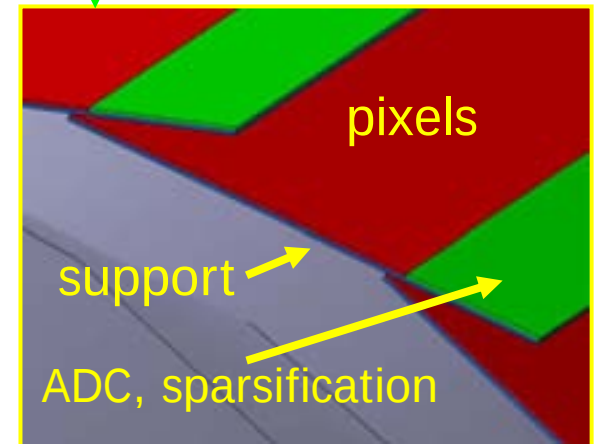
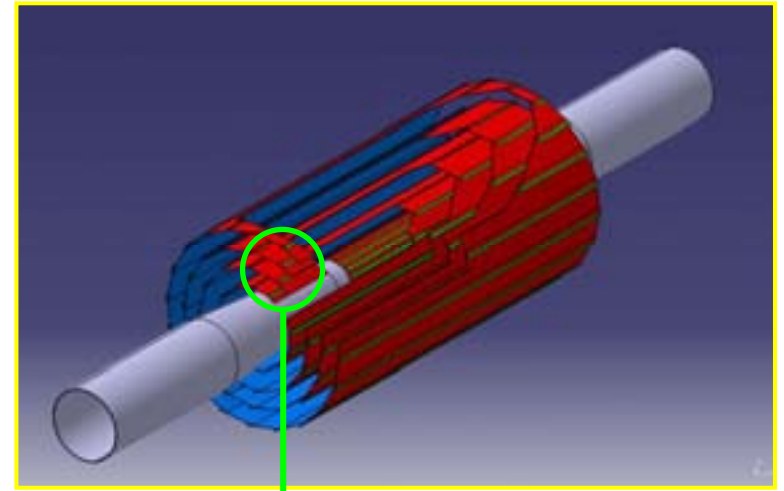
CMOS sensors in the ILC VD

Overall design a priori very similar to TESLA TDR concept (CCD):

- 5 cylindrical layer
- $R = 15 - 60$ mm
- surface ~ 3000 cm²

Basic characteristics:

- sensor thickness: ~ 25 - 50 μ m
- support thickness: ~ 50 μ m carbon fiber
- total number of pixels: $\blacklozenge$ 300 millions
- < 3 - 30 W (full detector, $1/200 - 1/20$ duty cycle)



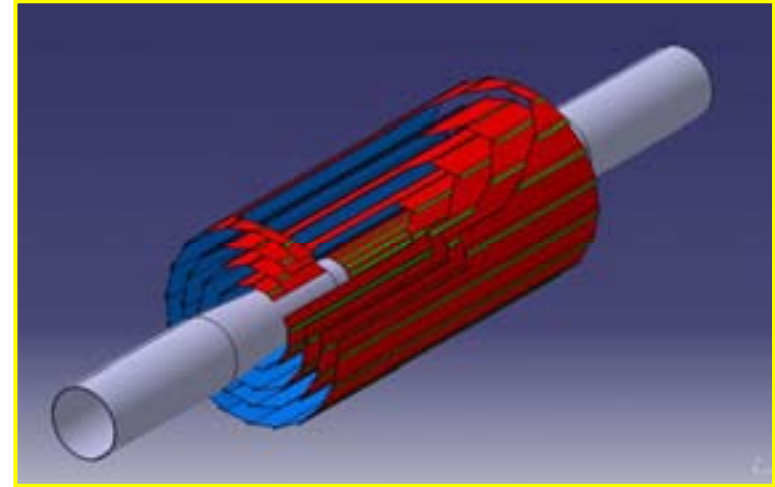
See talk of D. Grandjean for more details

Requirements on the sensors

Expect up to ~ 15 hits/cm²/BX from beamstrahlung

Readout speed required:

- ~ 25 μ s in Layer 0
- ~ 50 μ s in Layer 1
- < 200 μ s in Layer 2 - 4



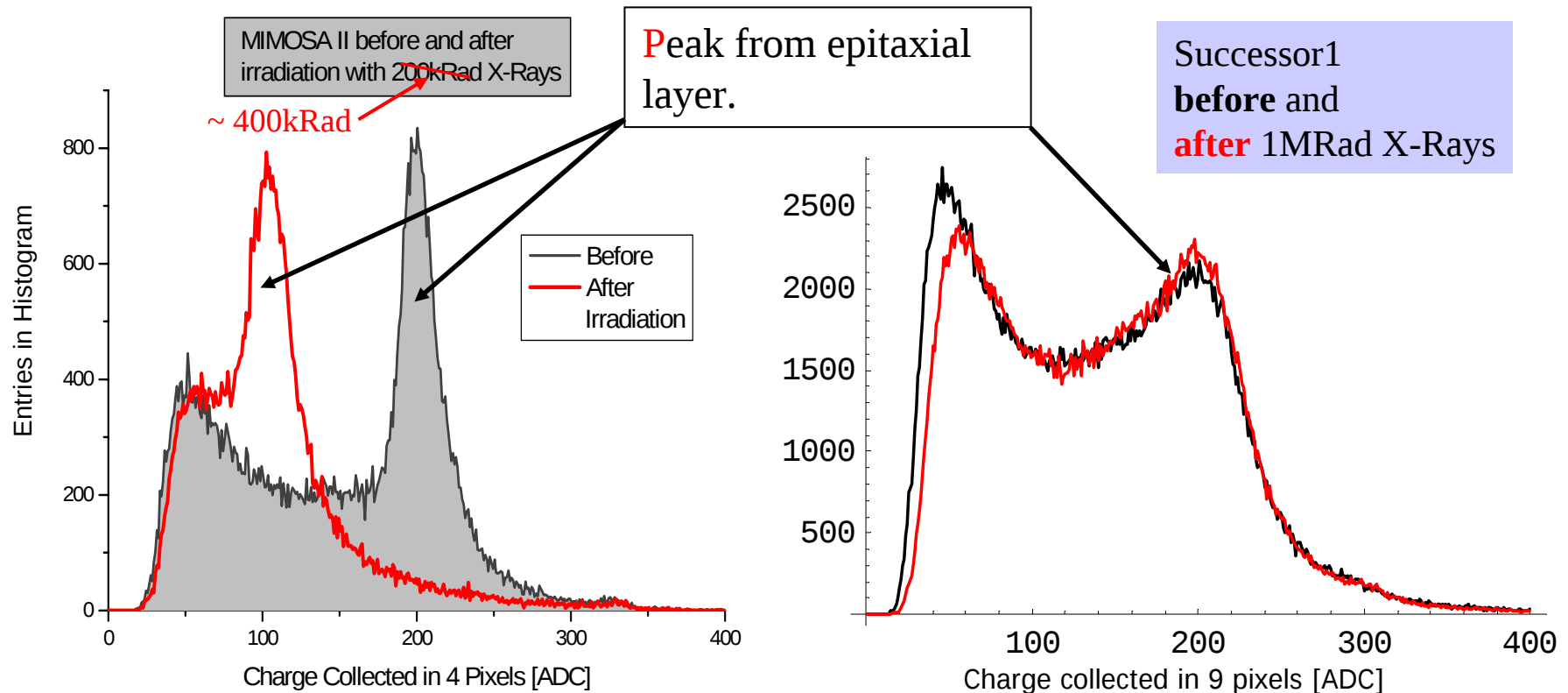
Corresponding radiation dose (3 years):

- $3 \times 10^{10} n_{eq}/\text{cm}^2$ due to neutron gas
(safety factor = 10)
- $6 \times 10^{12} e^{\pm} / \text{cm}^2$ due to beamstrahlung
($2 \times 10^{11} n_{eq}/\text{cm}^2$ with mean NIEL-Factor assumed = 1/30)
- Ionising damage: ≈ 50 kRad / year

See talk of D. Grandjean for more details

Status: Resistance against ionising doses

Testing the detector with an ^{55}Fe source before and after irradiation

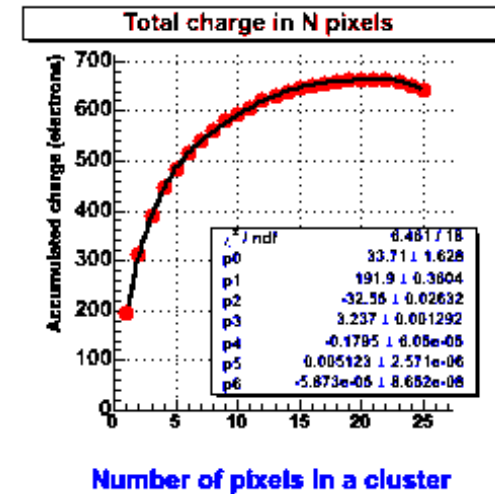
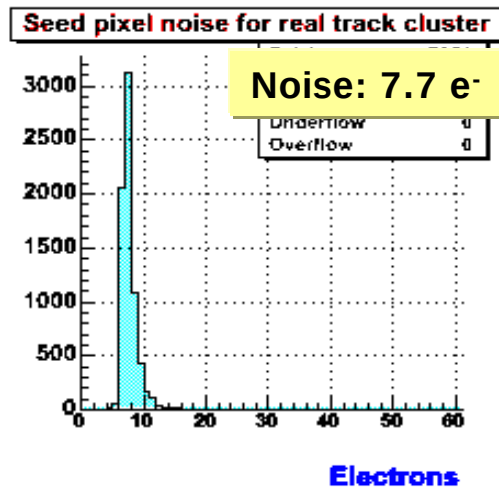
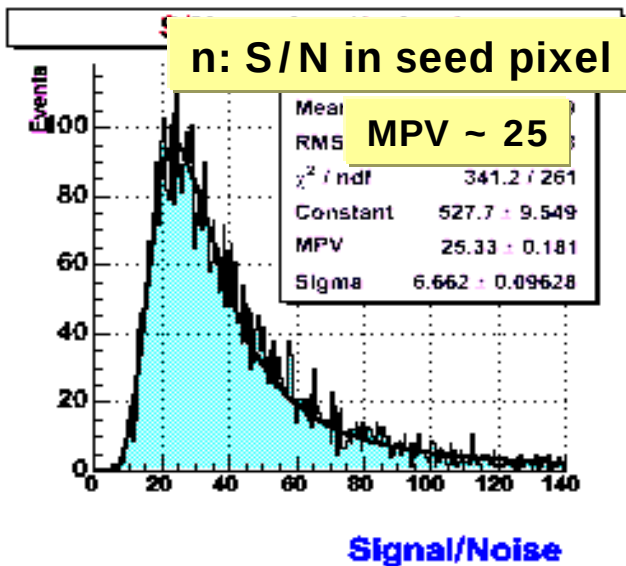


- First prototypes (MIMOSA2) were radiation soft.
- Key problem: Charge collection.
- Weak point has been identified and fixed in SUCCESSOR1 (SUCCESSOR 1 was provided by the SUCIMA coll. – FP5)

Assuming fast readout and moderate cooling, 1MRad can be tolerated.
Technology improvements for room temperature operation under study (Mi11,15)

Status: Tolerance to neutron irradiation

Beam test on MIMOSA9 irradiated with $10^{11} \text{ n}_{\text{eq}}/\text{cm}^2$ (1MeV)



Preliminary calibration

(Absolute numbers on S and N not valid, relative numbers and S/N OK)

20 μm pixel pitch, -20°C, 3.4 x 4.3 μm^2 diodes

Equivalent to ♦ 10 years of operation at the ILC:

- Efficiency: 99.97 +/- 0.02 %
- No obvious reduction in charge collection
- No obvious increase of noise (-20°C)

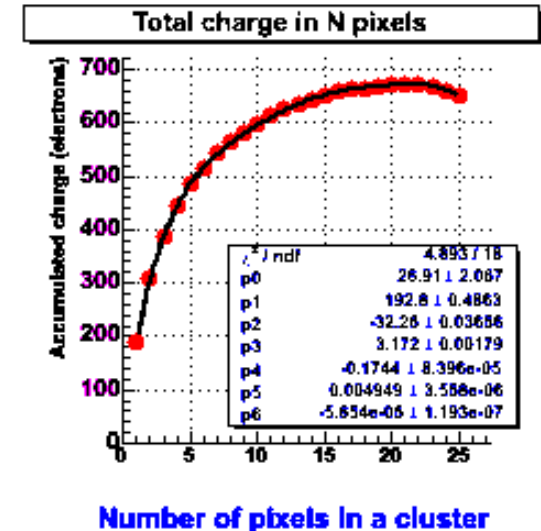
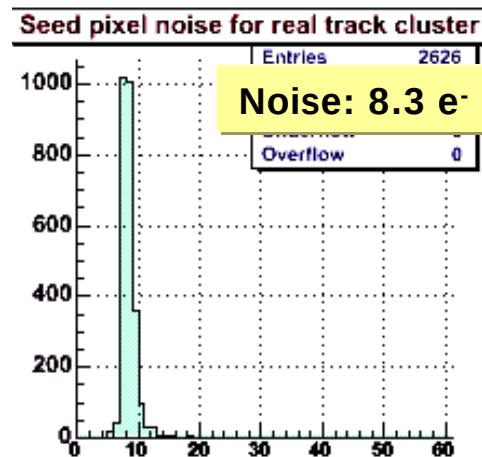
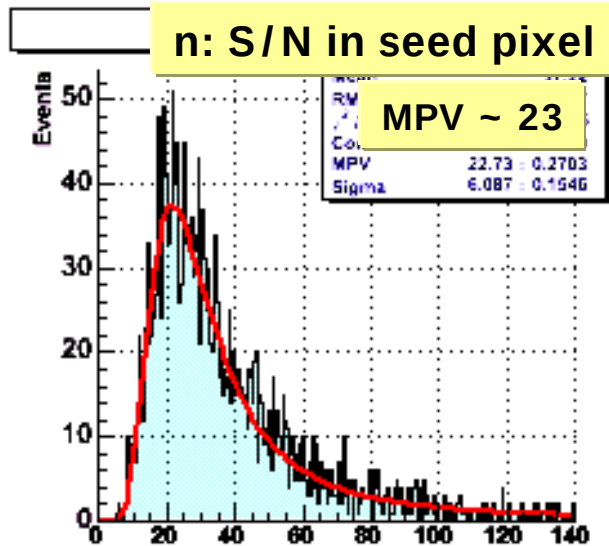
were observed.

S/N and detection efficiency remain excellent.

$10^{12} \text{ n}_{\text{eq}}/\text{cm}^2$ has also been tested with very good results

Status: Resistance against electron doses

Beam test on MIMOSA9 irradiated with 10^{13} e-/cm² (~10 MeV)



Preliminary calibration

Signal/Noise

(Absolute numbers on S and N not valid, relative numbers and S/N OK)

20 μ m pixel pitch, -20°C, 3.4 x 4.3 μ m² diodes

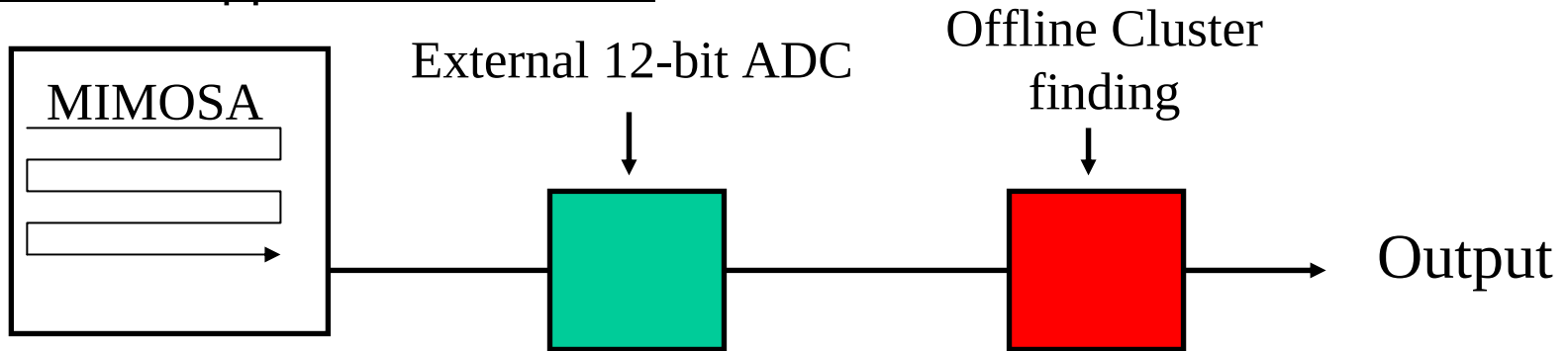
Equivalent to ♦ 5 years of operation in the ILC (with safety factor 3):

- Detection efficiency = 99.4 +/- 0.2 %
- Charge collection slightly degrades
- Noise slightly increases (-20°C).

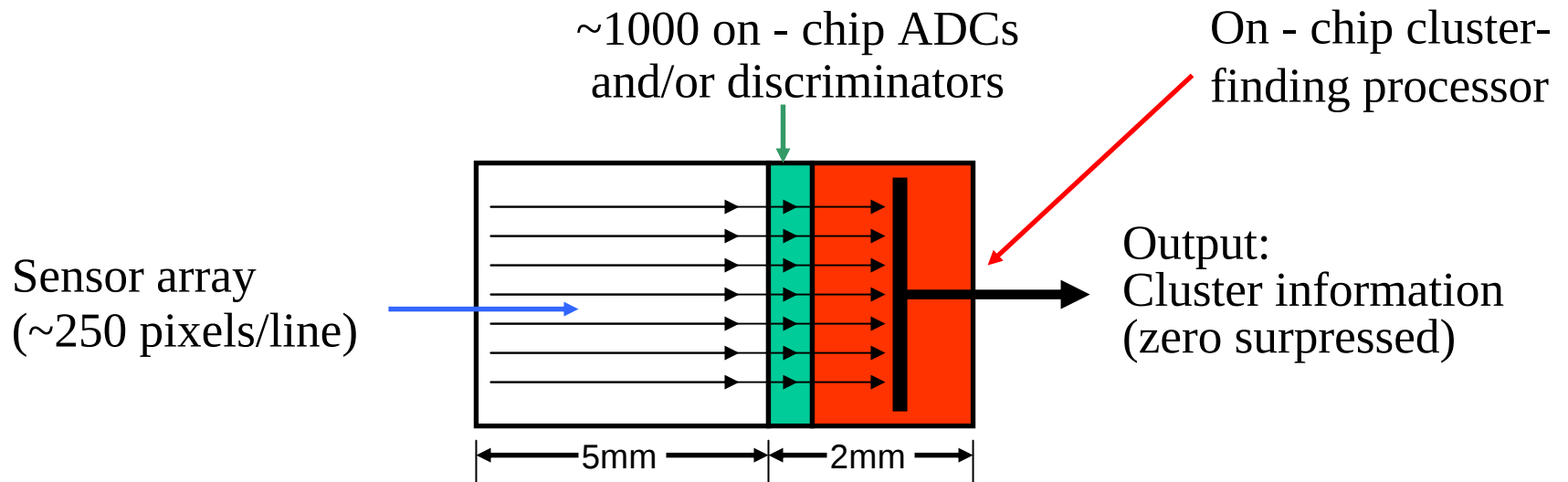
S/N and detection efficiency remain excellent

Fast readout speed, the inner layers

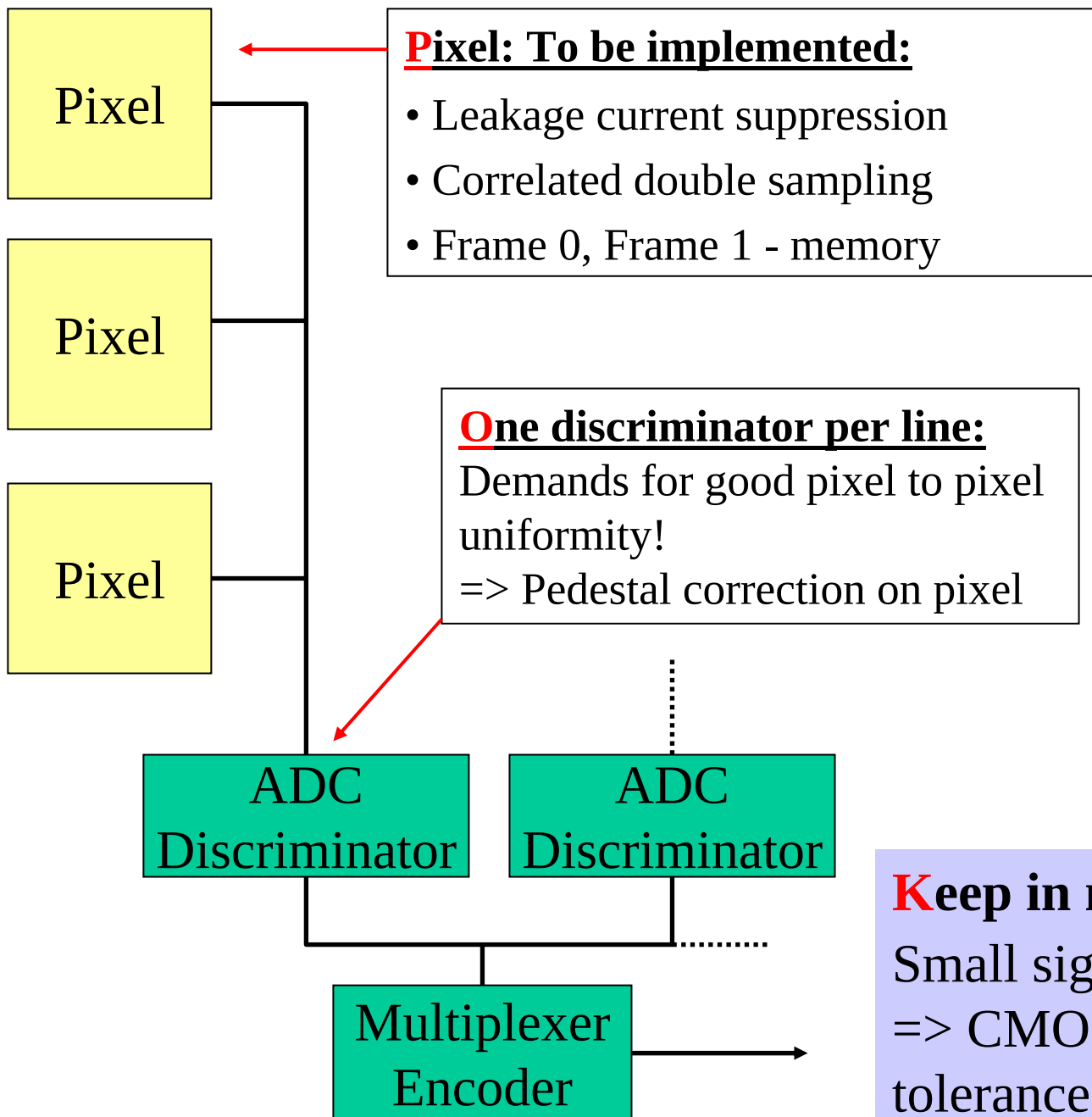
Standard approach for MAPS:



The design concept for the ILC inner layers:



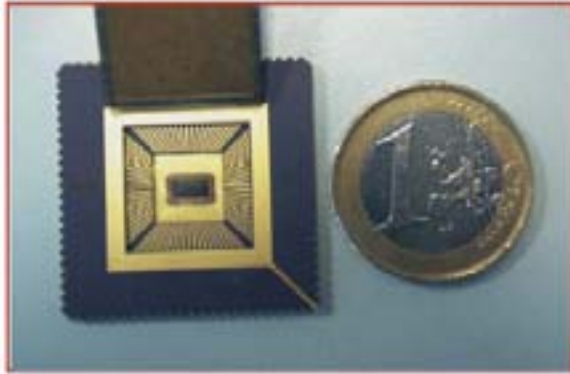
Goal: A readout time of ③ 25 μ s for the ILC



Keep in mind:

Small signals (a few $10^2 e^-$)
=> CMOS process fabrication tolerances are of relevance.

MIMOSA8, a MAPS with on - pixel CDS

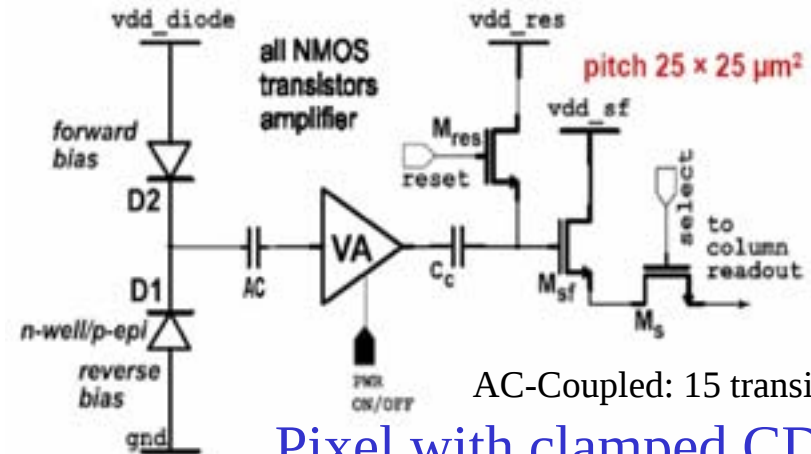


MIMOSA8

- TSMC 0.25 μ m process (8 μ m epi)
- 128 x 32 pixel
- On pixel CDS
- On chip discriminators
- fully parallel readout
- **20 μ s readout time (128 pixels)**

Preliminary results

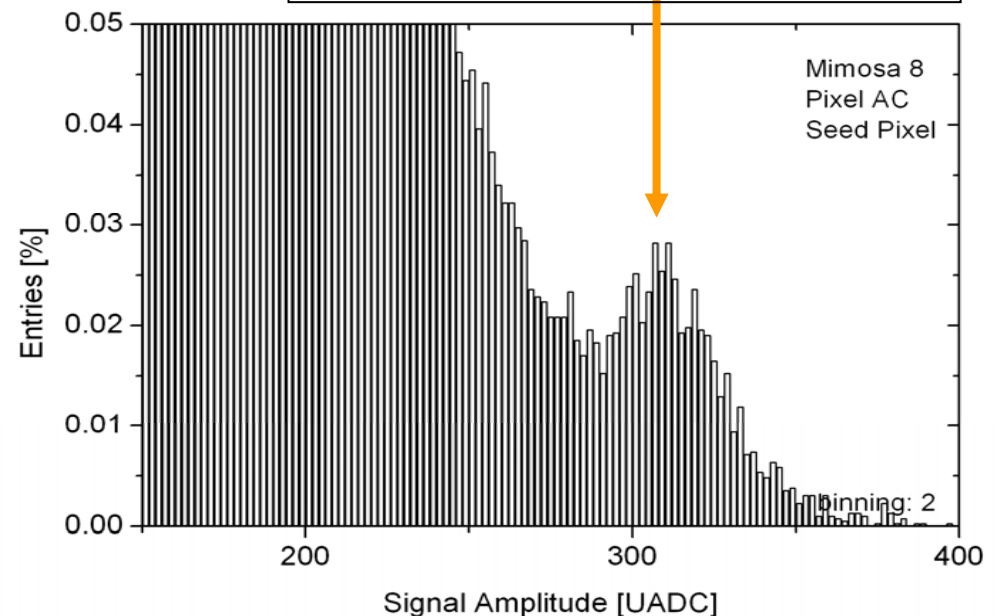
- Signal: ~ 50 - $110 \mu\text{V/e}^-$
- Noise: ~ 13 - $18 e^-$ (Pixel)
 ~ 3 - $8 e^-$ (Dispersion)
- CDS: OK
- Pedestal Correction: OK



AC-Coupled: 15 transistors

Pixel with clamped CDS

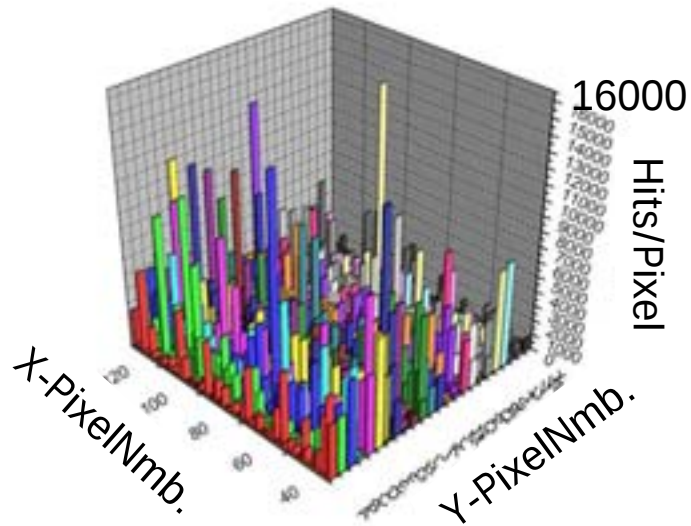
Clear calibration peak
 $\Rightarrow$ Low pixel to pixel dispersion



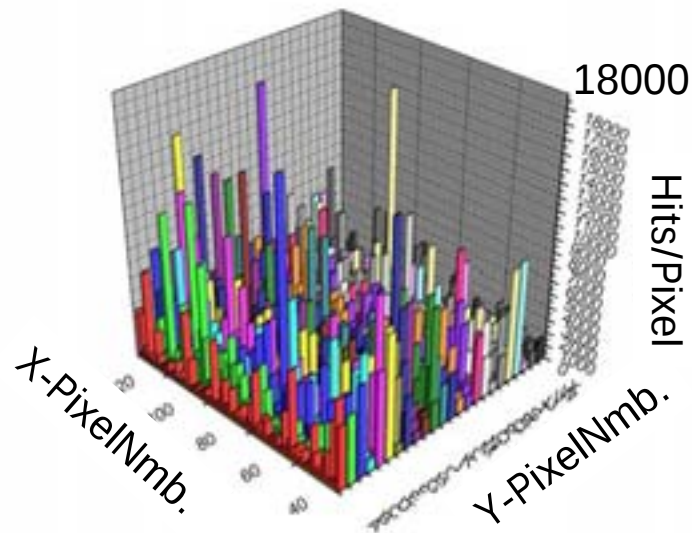
MIMOSA8: Discriminator tests

100kEvents

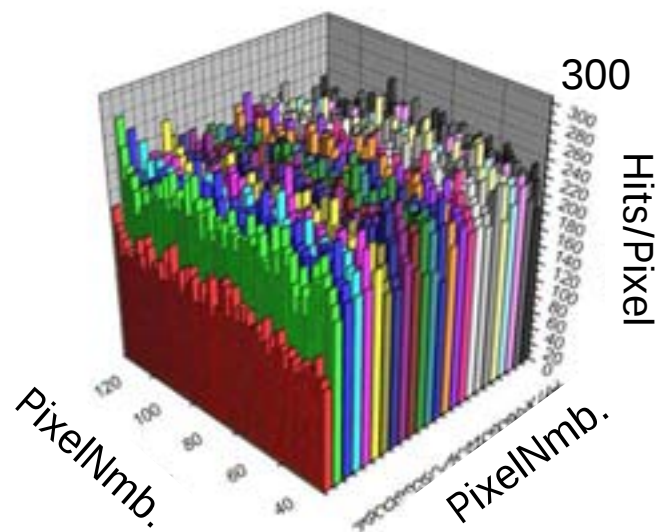
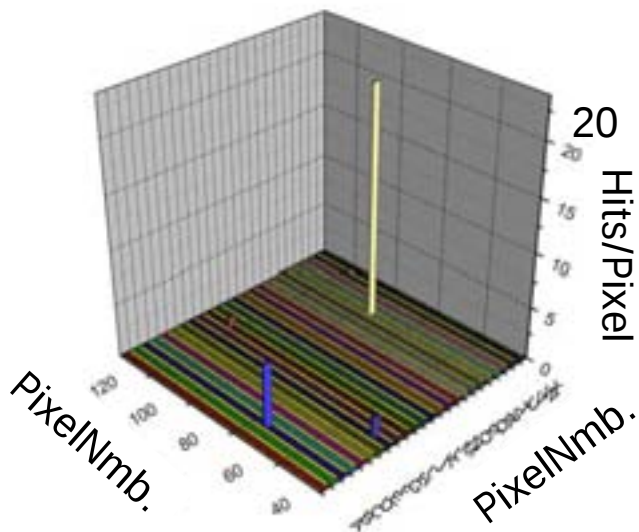
Without ^{55}Fe source



With ^{55}Fe source



$V_{\text{th}} = 5\text{mV}$



$V_{\text{th}} = 10\text{mV}$

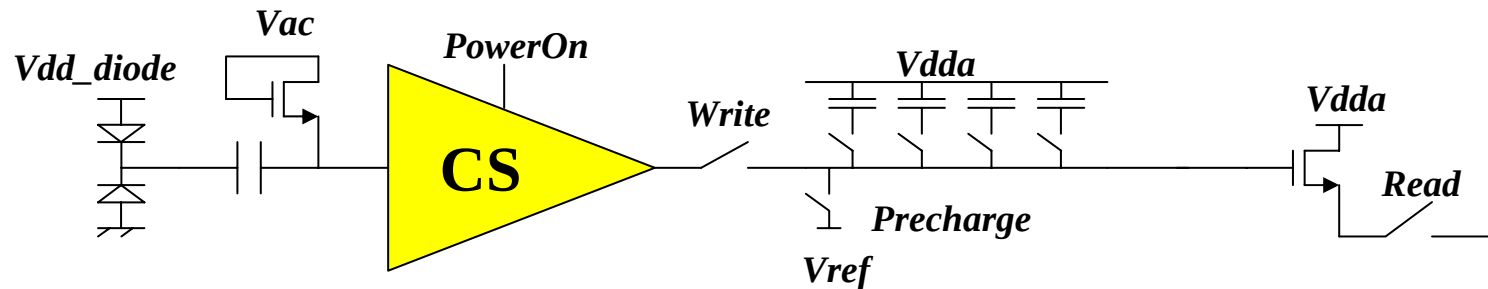
MIMOSA8: Integrated CDS + Discriminator

Next steps: Production of ADCs

- 4 – bit seem most adapted for the MAPS on chip ADCs
- Several dedicated designs are under study:
 - 2 ramp Wilkinson ADC, flash ADC, semi flash ADC, etc.
- Institutes involved in this development:
 - IReS (Strasbourg), LPCC (Clermont-Ferrand), LPSC (Grenoble), Dapnia (Saclay)

Status: First submissions are planned for September

Moderate readout speed: The outer layers



Basing on the FAPS-approach proposed by R. Turchetta:

Within a bunch train:

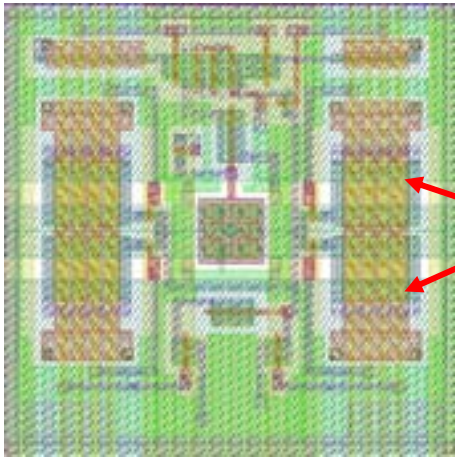
- Integrate charge with short integration time
- Save charge in analogue memory cells in the pixel (capacitors)

Readout memory cells slowly between the bunch trains.

-
- + Simpler readout due to reduced data flux
 - + Low complexity with respect to previous approach
 - Number of memory cells is limited by the size of the capacitor
 - This limits the readout speed (frames per bunch-train)

Most probably too slow for the inner layers but ok for the outer ones

MIMOSA-12: Multi memory cell pixels

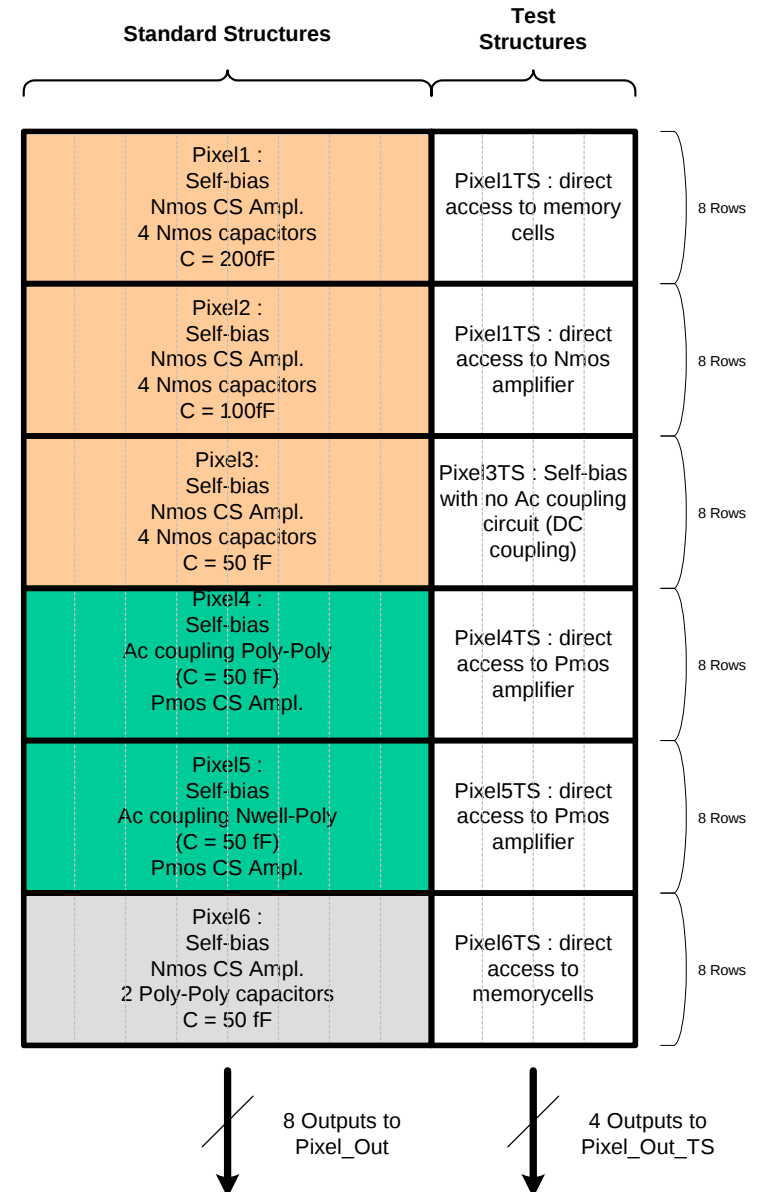


100 fF capacitor
(memory cell)

Mimosa-12 pixel

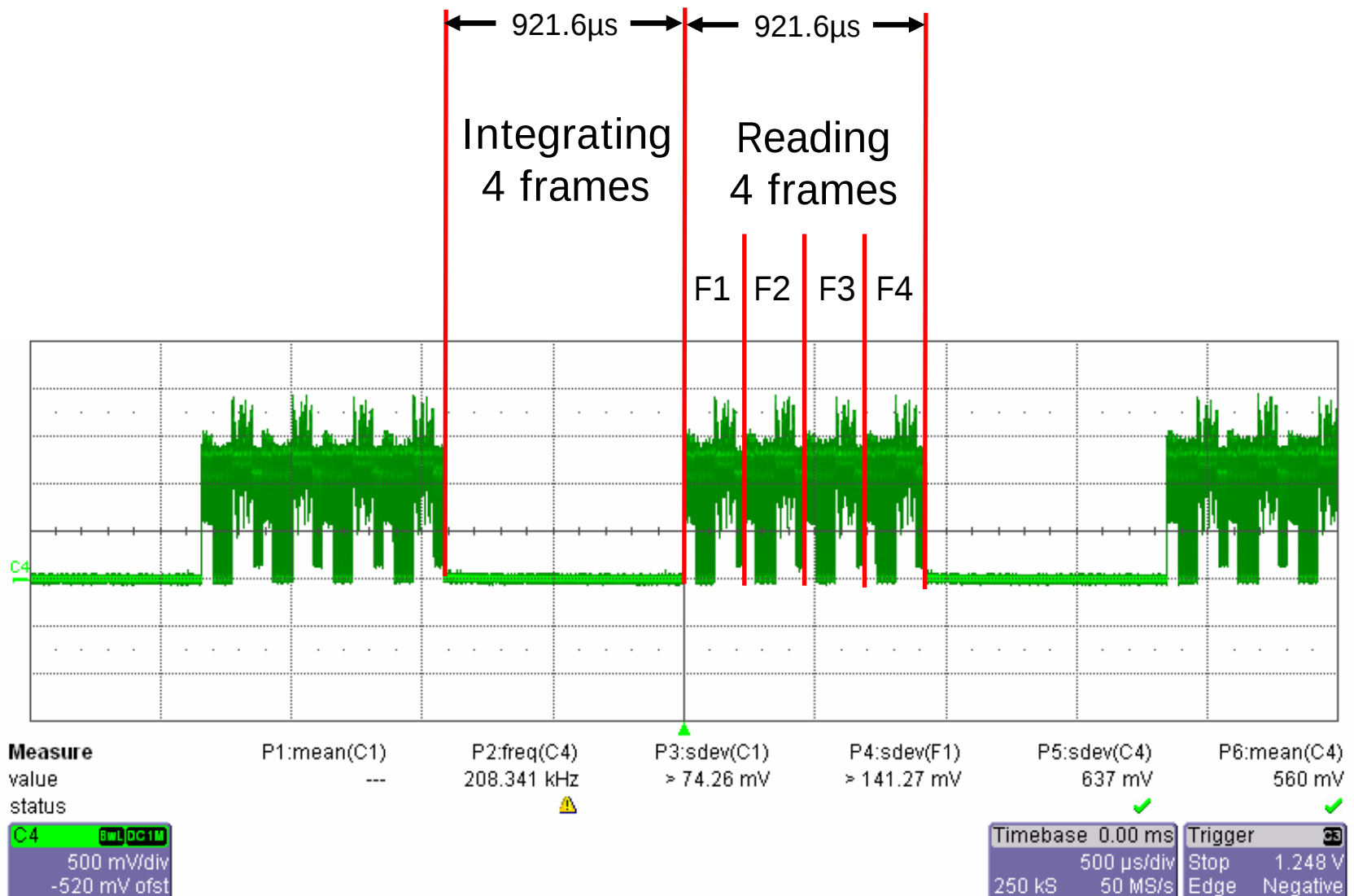
MIMOSA-12:

- AMS - 0.35 μm high resistivity
- 4 capacitors / pixel (35 μm pitch)
- 6 sub-arrays pixels with
50, 100, 200 fF capacitors
2 different amplifiers
1 clamping architecture
- 6 test structures (incomplete pixels
to test components)



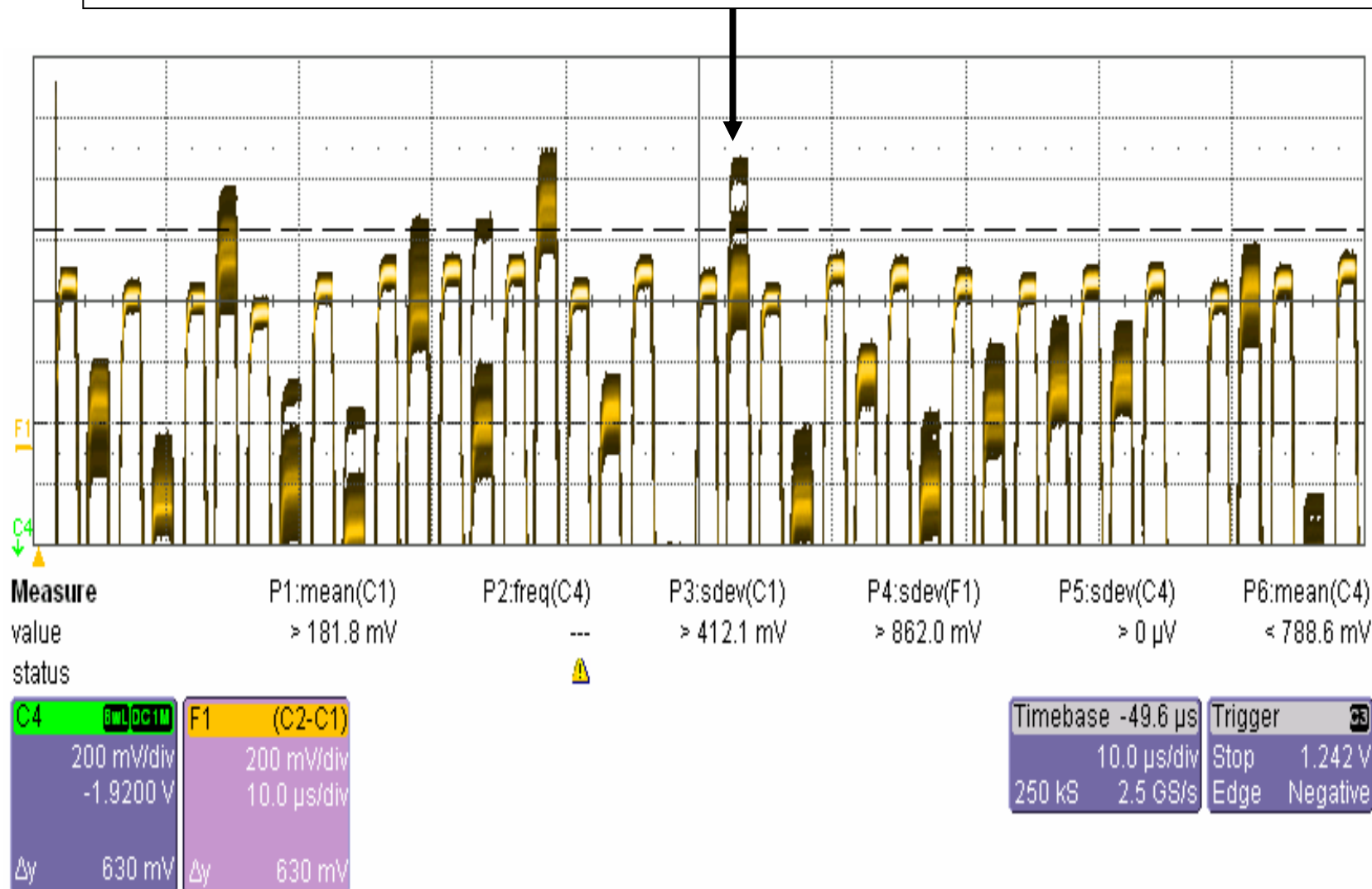
MIMOSA-12: Multi memory cell pixels

Very first tests with an oscilloscope:

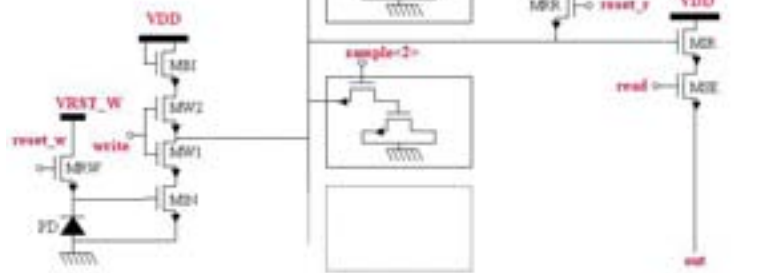
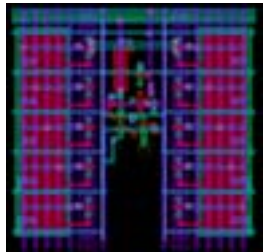


MIMOSA-12: Multi memory cell pixels

Hit from a ^{55}Fe source on pixel with internal gain 10x and 100fF



Flexible Active Pixel Sensor



10 memory cell per pixel

28 transistors per pixel

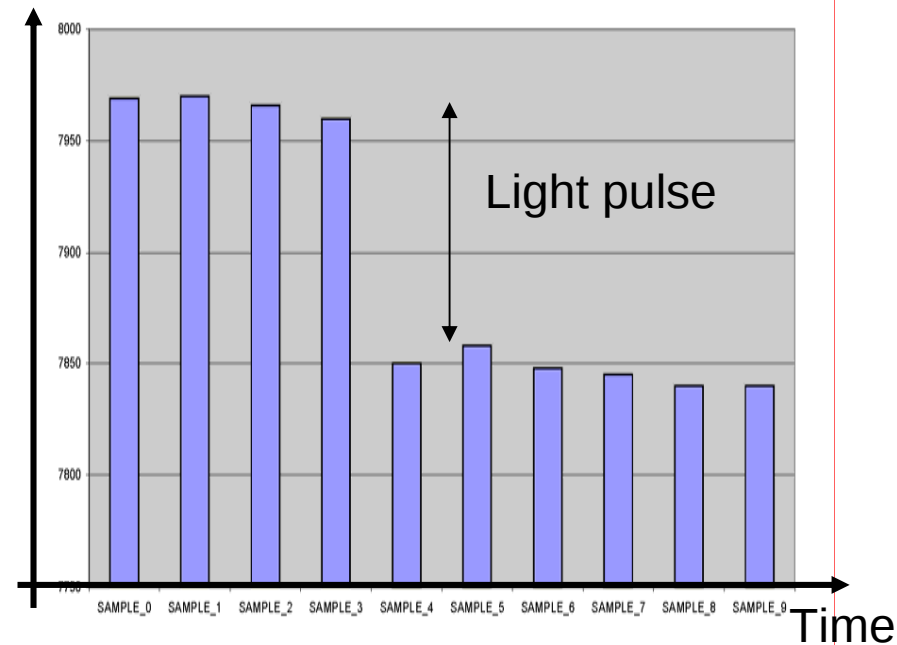
20 μm pitch

40x40 arrays

Design for the Vertex detector at the International Linear Collider

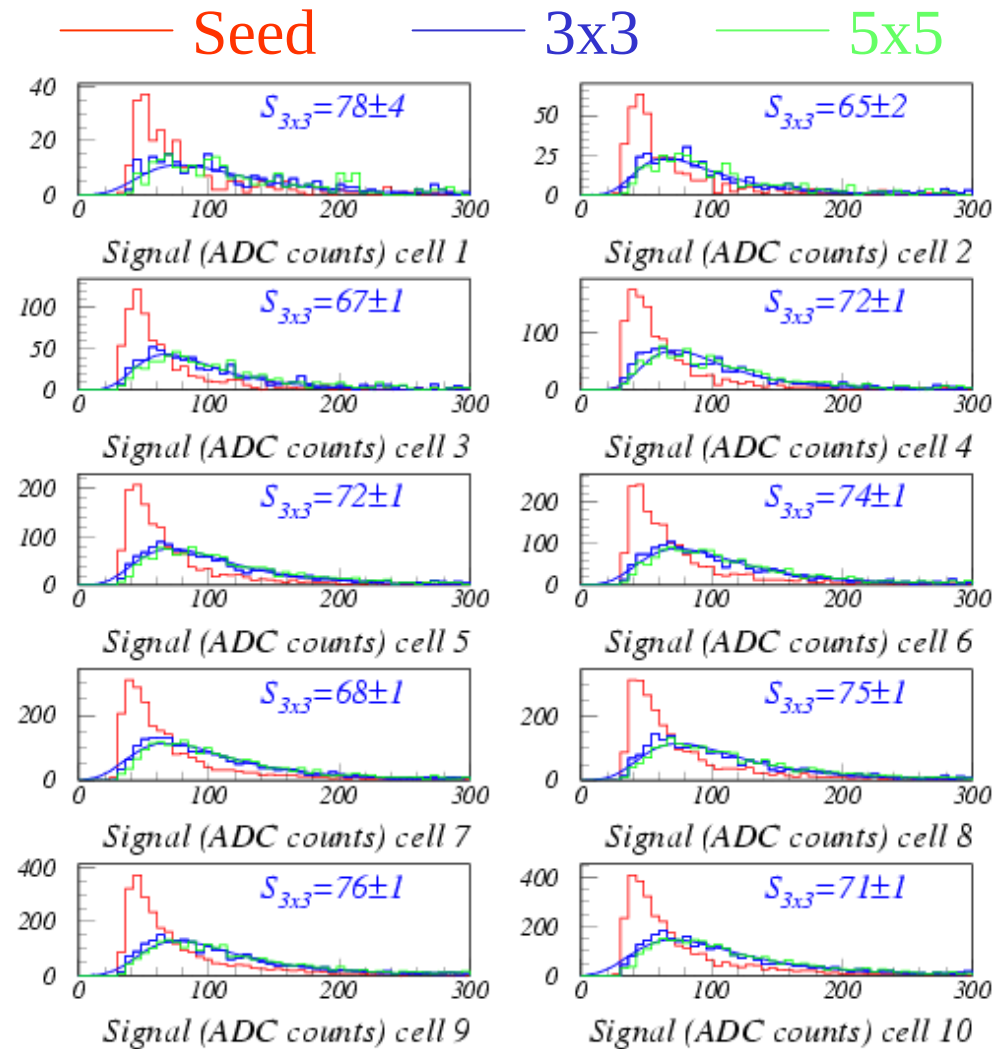
Pulses LED test

Amplitude



FAPS source test

- Source test
- Correlated Double Sampling readout (subtract $S_{\text{cell } 1}$)
- Correct remaining common mode and pedestal
- Calculate random noise
 - Sigma of pedestal and common mode corrected output
- Cluster definition
 - Signal $> 8\sigma$ seed
 - Signal $> 2\sigma$ next
- Note hit in cell i also present in cell $i+1$.
- S/N_{cell} between 14.7 ± 0.4 and 17.0 ± 0.3



Other development lines

MIMOSar2:

- 128x128 pixels, 30 μ m pitch,
- 4ms readout time (serial readout).
- Optimized for Star running conditions (+40°C)

Status: To be tested

MIMOSA11:

- 4x42x42 pixels, 30 μ m pitch, serial readout.
- Driven by requirements of FAIR/CBM
- Optimized for radiation tolerance $\gg$ 1MRad

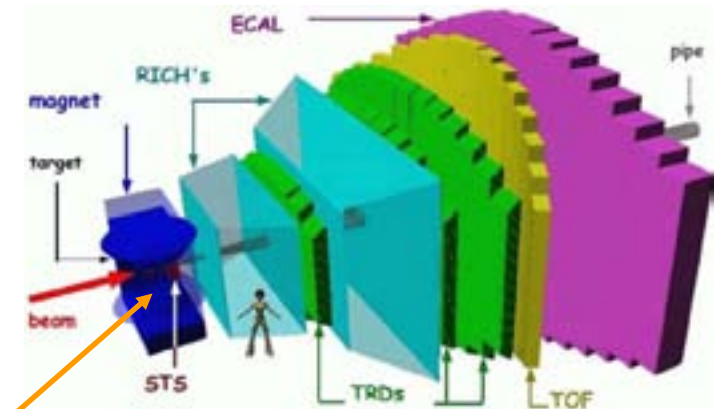
Status: Promising beamtest has been done.

Radiation tolerance under study

MIMOSA15:

- Even more radiation tolerant pixels then in MI-11.
- Pixels with optimized clamping.
- Pixels with new sensors in current mode
- Pixels optimized for electron microscopes*

Status: Submitted for production



CBM @ GSI / Darmstadt

Exploration of the nuclear phase space diagram.

www.gsi.de/fair/experiments/CBM

MIMOSA13:

- Readout in current mode
- Optimized readout speed

Status: To be tested

EUDET telescope:

- Macroscopic prototype
- Digital readout

Status: Planned for 2007

* As proposed by P.Rehak, BNL

UK-MAPS: Conclusion and Plans

Parametric test sensors used to test new designs, noise, rad hardness
MIP detection with good S/N for 3-4 MOS devices, up to $>10^{14}$ p cm⁻²
MIP detection with good S/N for FAPS

Beam test on RAL_HEPAPS2 (3/4MOS, FAPS, irradiated sensors) → under study

RAL_HEPAPS4. Large sensor ($\sim 1k \times 384$), rad-hard, high speed (5 MHz per row) → in production

Future: Working with LCFI to investigate in-pixel storage architecture (FAPS) for the ILC

Summary and Conclusion

Radiation doses on the ILC- VTX – detector (3 years):

- ③ $3 \times 10^{10} n_{eq}/cm^2$ due to neutron gas
- ③ $6 \times 10^{12} e^\pm /cm^2$ due to beamstrahlung ($2 \times 10^{11} n_{eq}/cm^2$)
- ③ Ionising damage: ③ 150 kRad

Radiation hardness of CMOS-Sensors:

- $> 10^{12} n_{eq}/cm^2$ against neutrons
- $> 10^{13} e/cm^2$ against 10 MeV electrons
- > 1 MRad against soft X - Rays

CMOs sensors stand ILC radiation doses, even if they happen to be much above the MC-predictions*.

* So far with moderate cooling, R&D under way to operate safely at room temperature.

Performances with intelligent pixels (CDS => more noise) still to be assessed

Summary and Conclusion

Readout speed requirements:

- $\sim 25 \mu\text{s}$ for the inner layer, $\sim 50 \mu\text{s}$ in the second one
- $< 200 \mu\text{s}$ for the outer layers

Readout speed of CMOS-Sensors:

Detectors with integrated data sparsification:

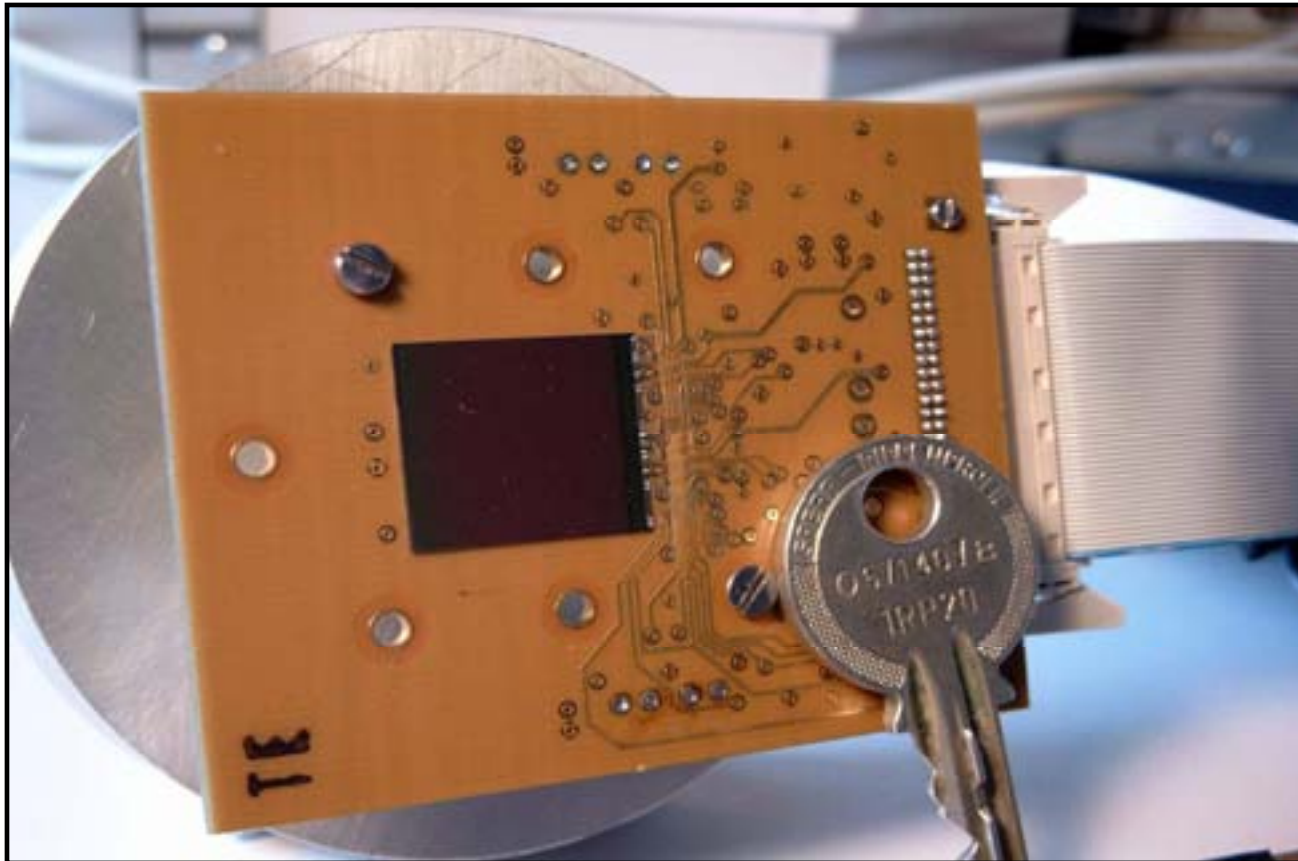
- $\sim 20 \mu\text{s}$ reached with Mi8 (128 pixels/col, On-chip CDS and discri.)
- Very promising results for S/N and discriminator function
- Beam test foreseen in September
- ADC-designs now under study (first submissions planned in Sept.)

Detectors relying on FAPS approach (On-pixel memory cells):

- A first detector has been built.
- Analogue and digital structures work.
- First hits were seen (prove of principle) on oscilloscope.
- Refined tests are under preparation

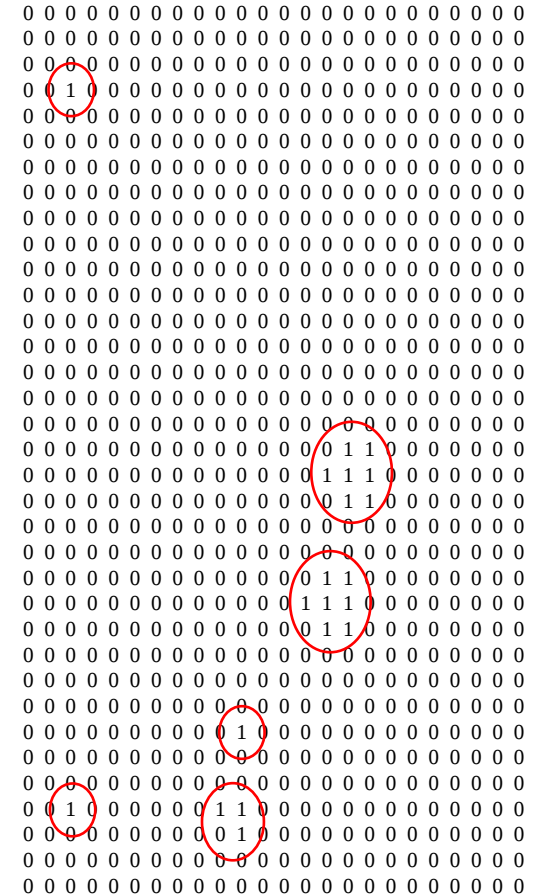
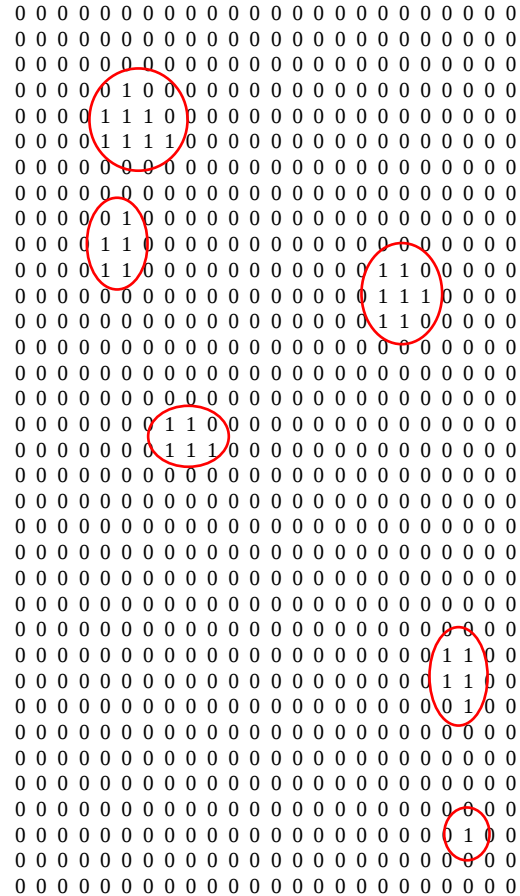
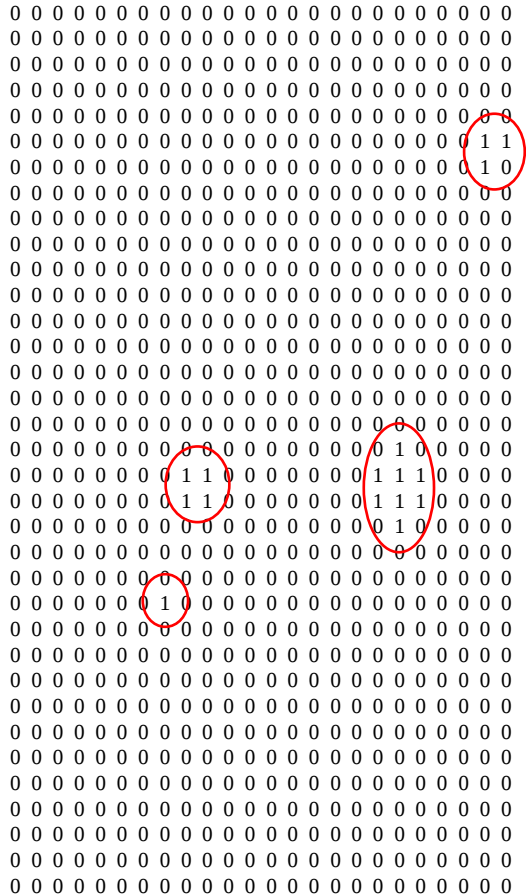
Design of a fast architecture is on a good way ($\Rightarrow$ EUDet 2007).

Thank you



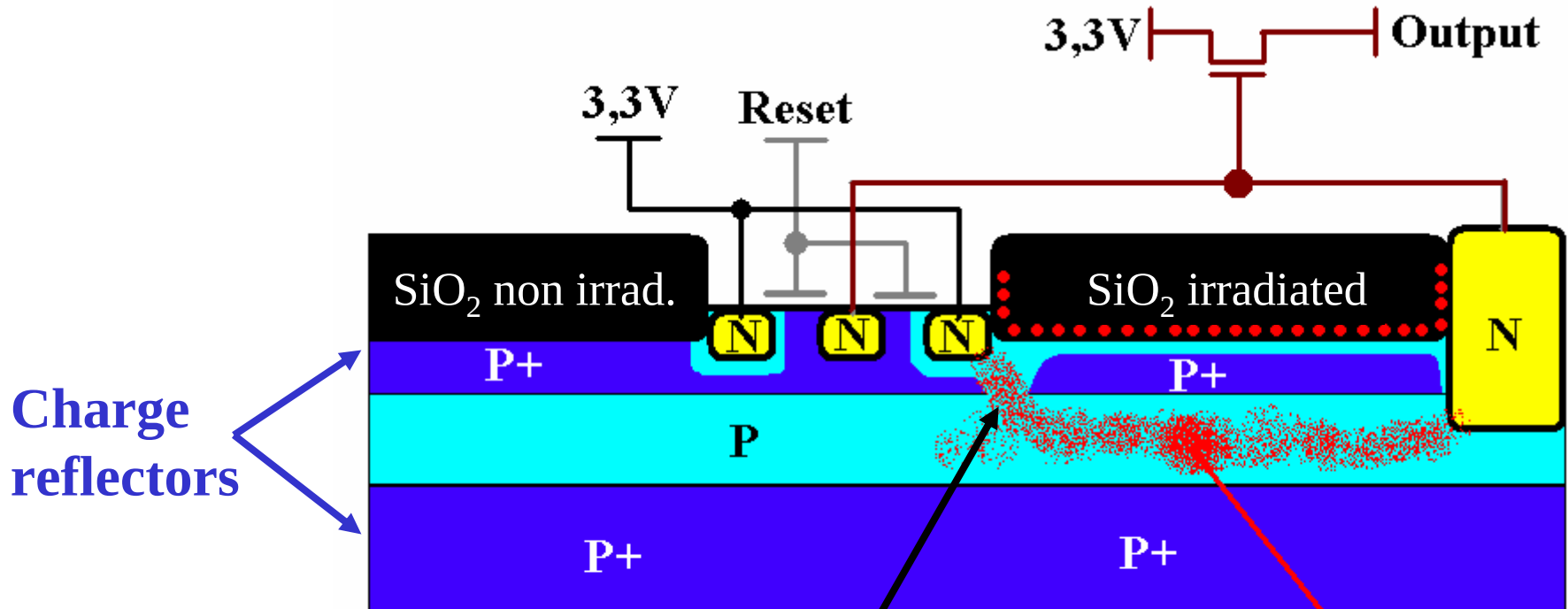
MIMOSA V

1 MegaPixel, resolution $< 2\mu\text{m}$

MIMOSA8 ($f_{ck} = 7.5\text{MHz}$, $V_{th} = +6\text{mV}$)

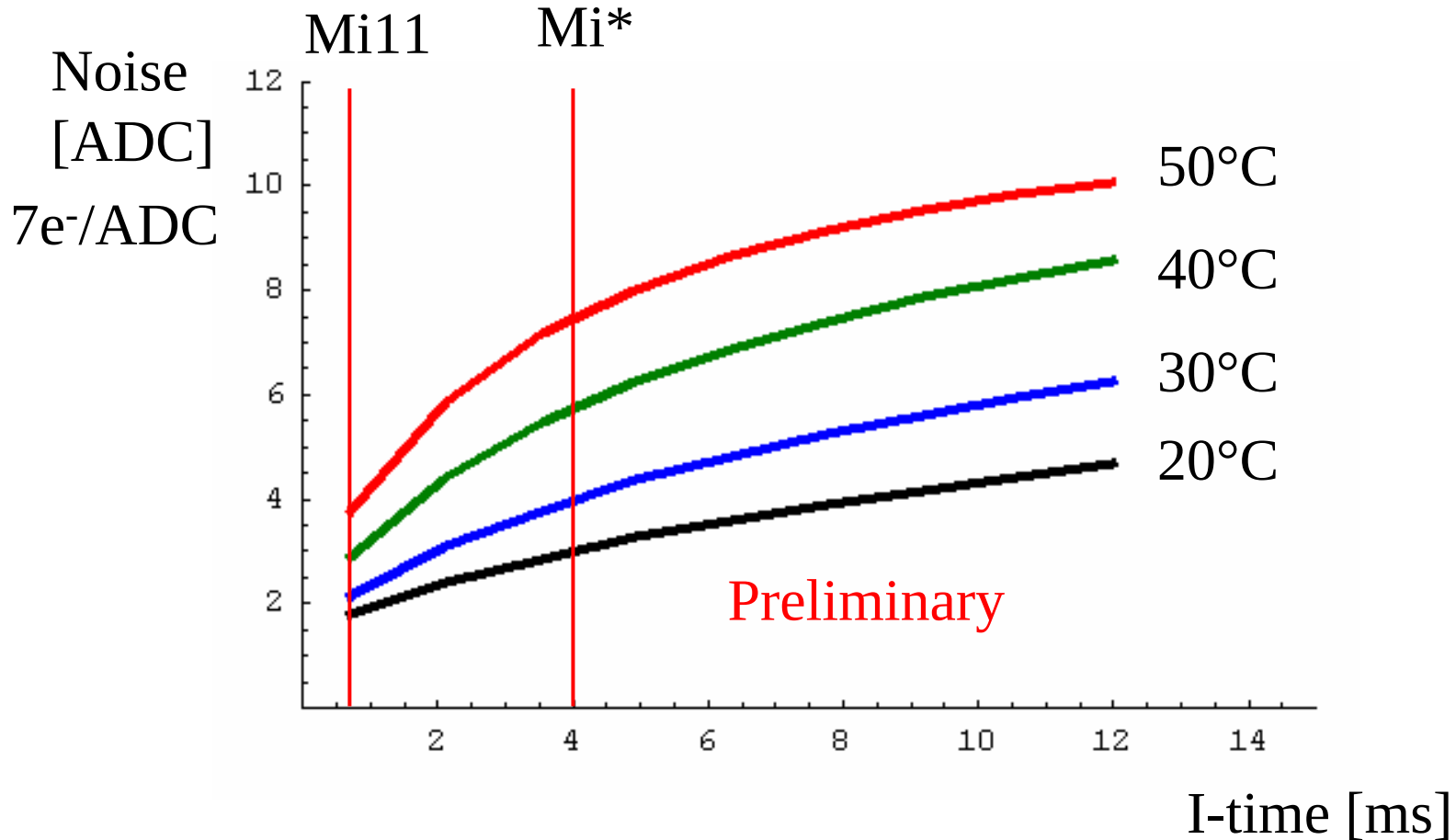
A working hypothesis:

!!Pixel without RESET-Transistor stays OK!!



- **R**eset transistor + positive charge create locally high fields.
- **P**-Well barrier gets depleted.
- **P**arasitic charge collection by the Reset-Transistor.

Result on A0, Sub1 after 23kRad



What stands MAPS for?

CMOS – Monolithic Active Pixel Sensors

Monolithic:

Read-out electronics and sensors are integrated on the same substrate.

Active Pixel :

An amplifier is integrated into each pixel

Sensor

MAPS were developed for visible light applications by industry.

MAPS are produced with cheap standard CMOS-processes.

The operation principle of MAPS

Sensor design:

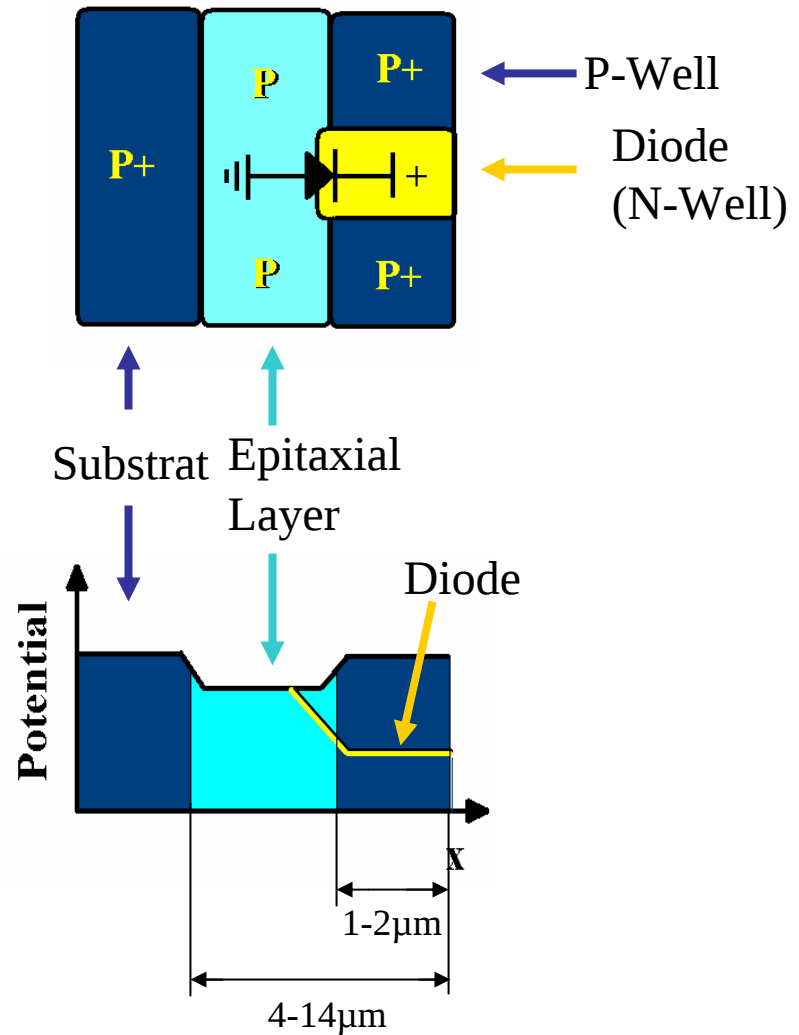
A

Minimum

Ionising

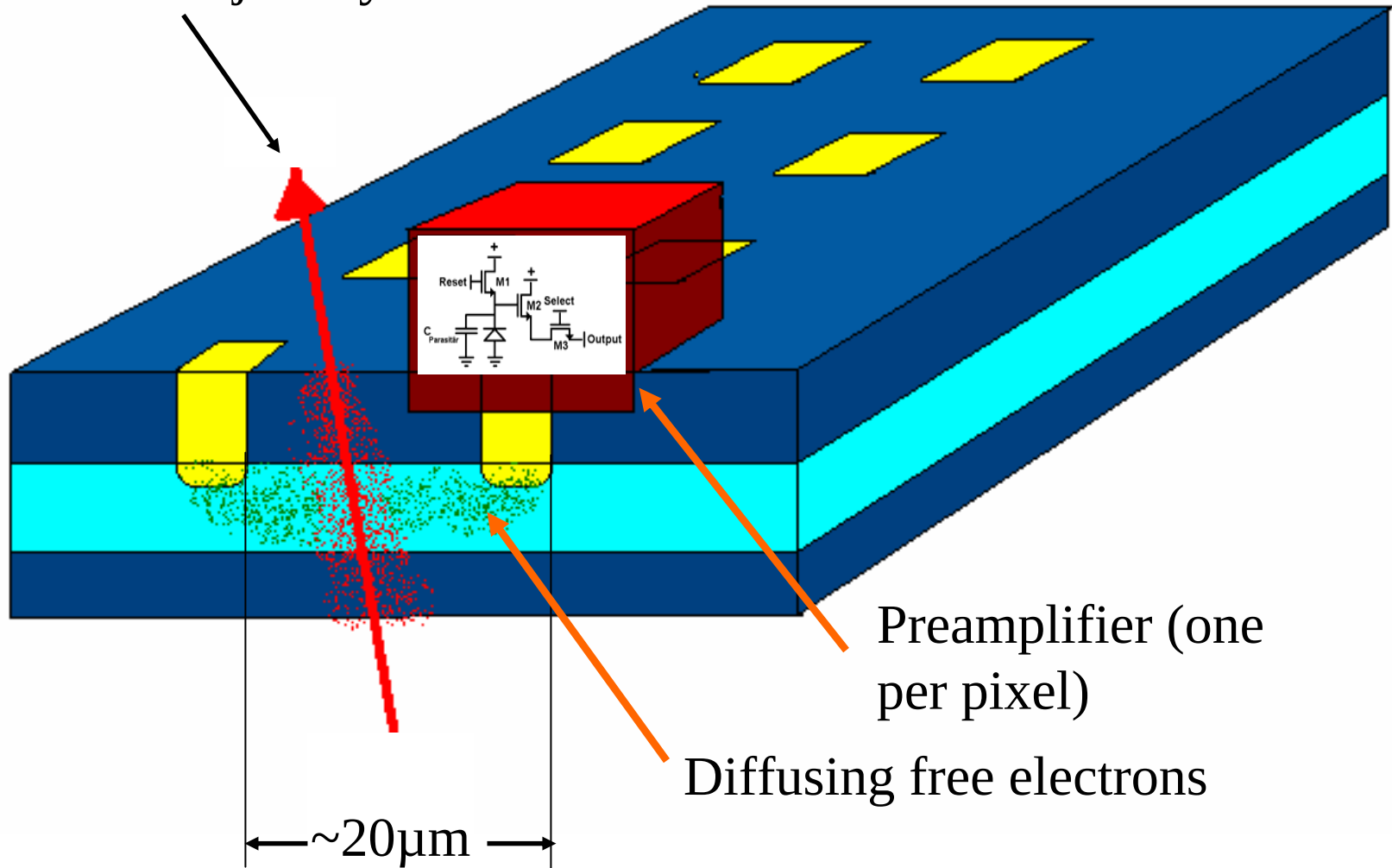
Particle creates

~ 80 e⁻/h-pairs per μm in Si

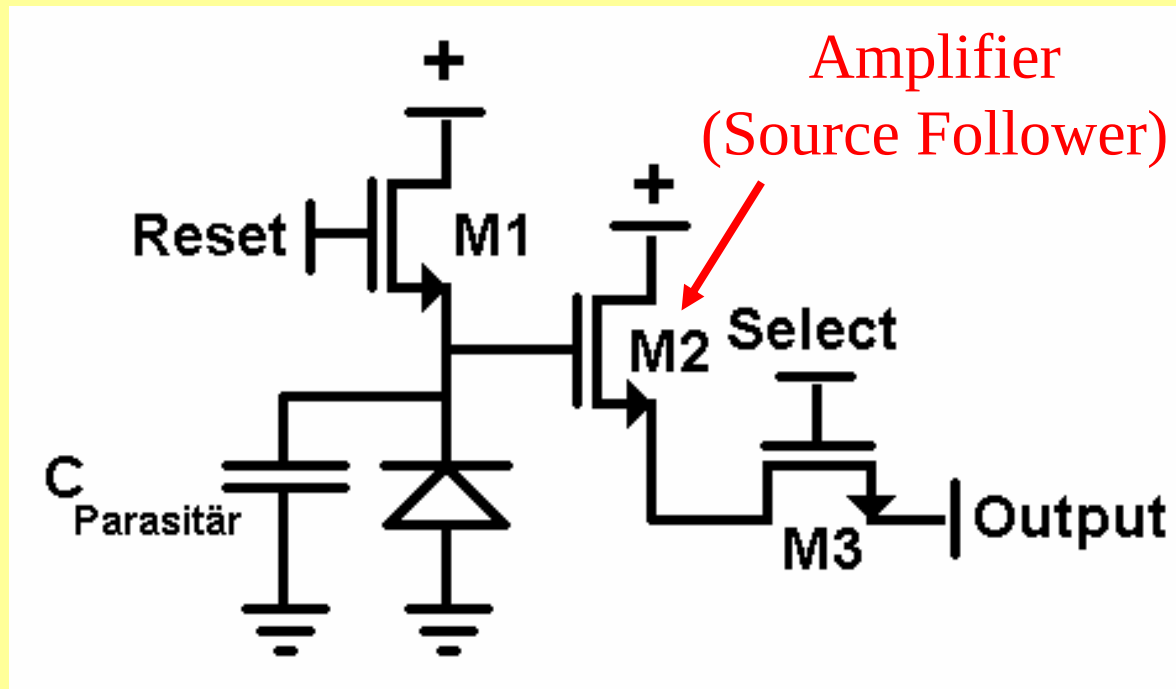


The operation principle of MAPS

Particle trajectory

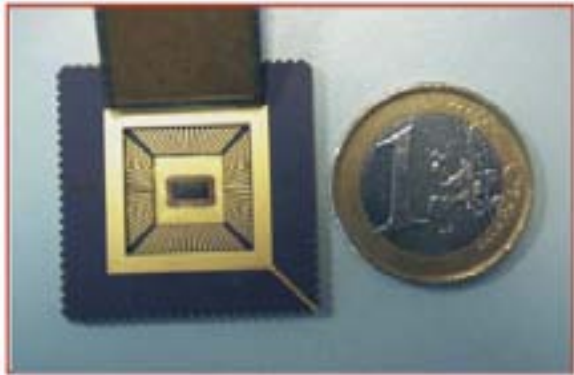


The operation principle of MAPS



Layout of a classical Active Pixel (simplified)

MIMOSA8: Analogue tests with ^{55}Fe source

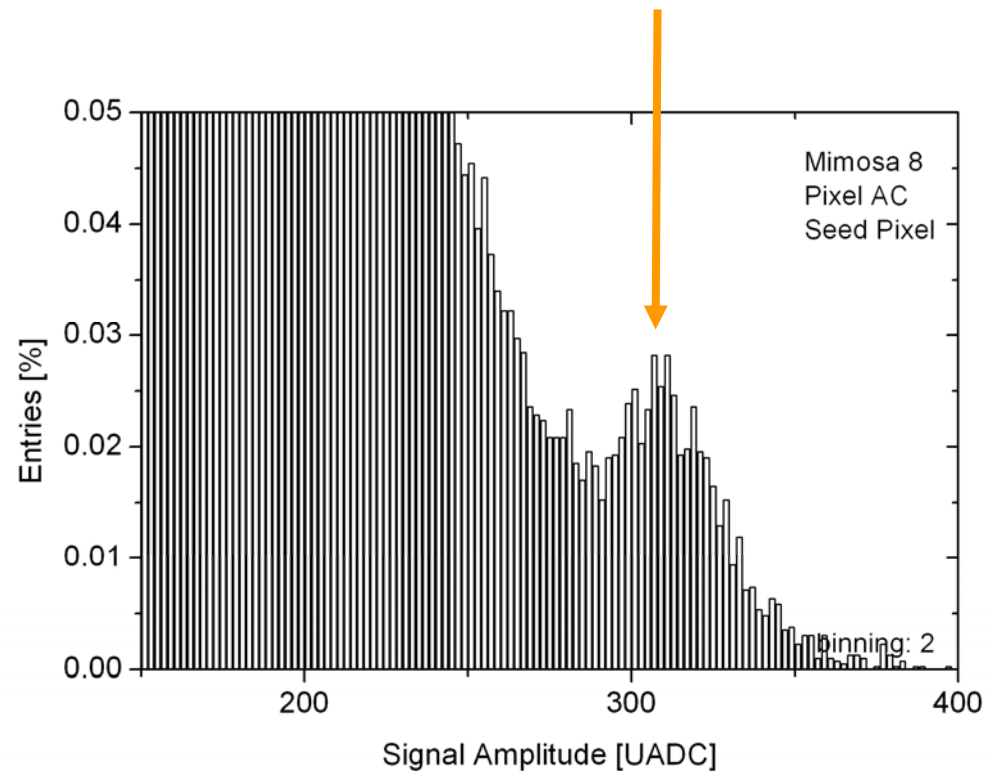


In collaboration with CEA/DAPNIA

Clear calibration peak
=> Low pixel to pixel dispersion

Preliminary results

- Signal: $\sim 50\text{-}110 \mu\text{V}/e^-$
- Noise: $\sim 13\text{-}18 e^-$ (Pixel)
 $\sim 3\text{-}10 e^-$ (Dispersion)
- CDS: OK
- Pedestal Correction: OK



See also: Y. Degerli et al, Proc. of the 2004 IEEE NSS conference, Roma

Outline

33 million pixels in a box

- Which performances are reached?

The vertex detector concept

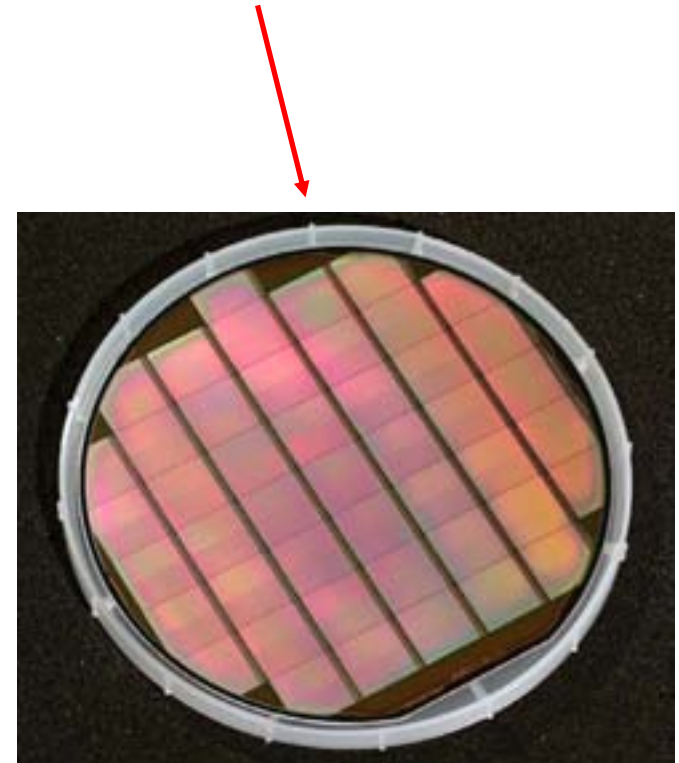
- A short reminder
- Requirements on readout speed
- Requirements on radiation hardness

Radiation hardness

- State of the art
- Recent results

Readout speed

- The problem
- A concept for fast MAPS
- Achievements and milestones



A MIMOSA5 Wafer
33 x 1MPixel
120 μ m thickness